



#### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

33 A

#### **Features**

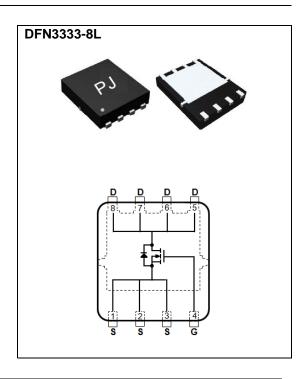
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@15A<21mΩ
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@8A<24m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60		
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	Tc=25°C	I <sub>D</sub>	33		
	T <sub>C</sub> =100°C		21	Α	
Pulsed Drain Current(Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	132		
Power Dissipation	T <sub>C</sub> =25°C	Po	44.6	10/	
	Tc=100°C		18	W	
Continuous Drain Current	T <sub>A</sub> =25°C	lο	6		
	T <sub>A</sub> =70°C		5	Α	
Power Dissipation	T <sub>A</sub> =25°C		2.0	W	
Power Dissipation	T <sub>A</sub> =70°C	Pb	1.3		
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		Eas	42	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	R <sub>0</sub> JC	2.8	°C/W	
	Junction to Ambient	R <sub>0JA</sub>	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0	1.73	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	18	21	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A	-	21	24	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1.0	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic <sup>(Note 5)</sup>			_			
Total Gate Charge	$Q_g$	V <sub>DS</sub> =30V, I <sub>D</sub> =15A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	28	-	nC
Gate-Source Charge	$Q_gs$		-	3.5	-	
Gate-Drain Charge	$Q_{gd}$		-	6.5	-	
Input Capacitance	Ciss	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1680	-	pF
Output Capacitance	Coss		-	115	-	
Reverse Transfer Capacitance	Crss	I=1.0IVINZ	-	85	-	
Turn-On Delay Time	td <sub>(on)</sub>	\/ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	7.2	-	
Turn-On Rise Time	<b>t</b> r	V <sub>DD</sub> =30V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω (Note 1,2)	-	38	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	34	-	
Turn-Off Fall Time	t <sub>f</sub>	(10.00 1,2)	-	8.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I.		-	-	33	А
Diode Forward Current	Is					
Reverse Recovery Time	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.68	1	V

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. The test condition is L=0.1mH,  $I_{AS}$ =29A,  $V_{DD}$ =25V,  $V_{GS}$ =10V, Starting  $T_J$ =25°C
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

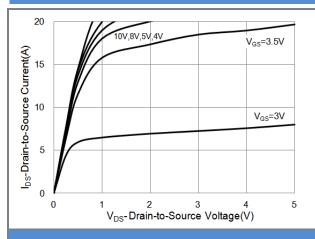
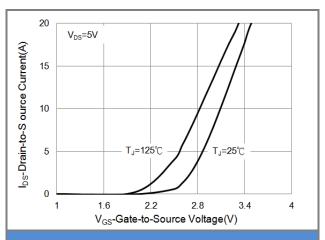


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

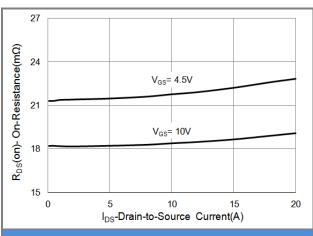


Fig.3 On-Resistance vs. Drain Current

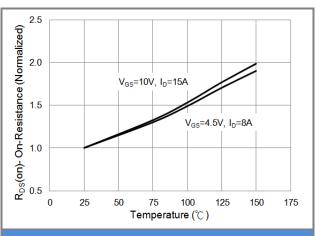


Fig.4 On-Resistance vs. Junction temperature

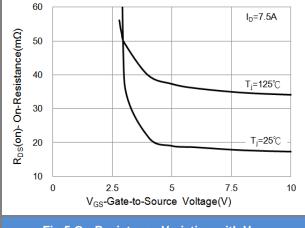


Fig.5 On-Resistance Variation with V<sub>GS</sub>

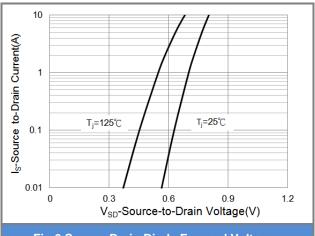


Fig.6 Source-Drain Diode Forward Voltage





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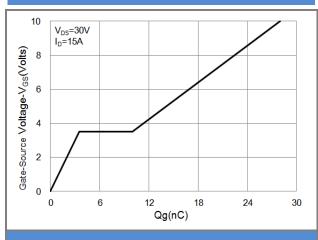


Fig.7 Gate-Charge Characteristics

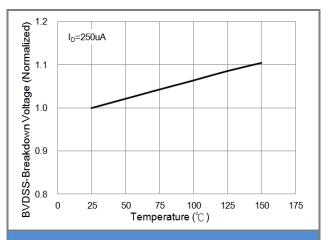


Fig.8 Breakdown Voltage Variation vs. Temperature

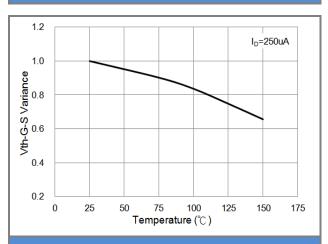


Fig.9 Threshold Voltage Variation with Temperature

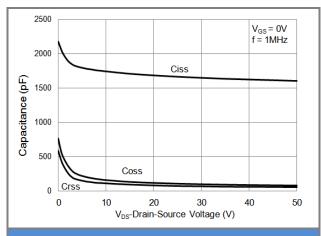
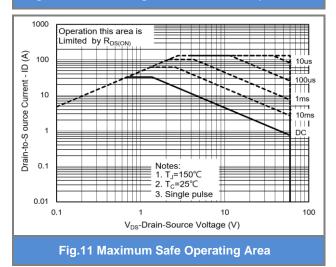


Fig.10 Capacitance vs. Drain-Source Voltage







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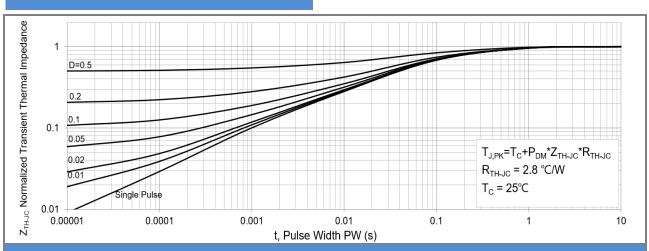


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

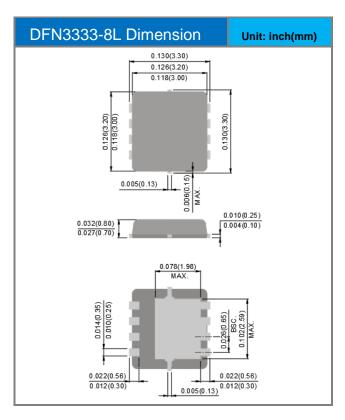


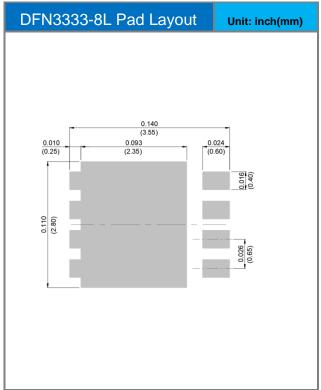


### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4466AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4466	Halogen free RoHS compliant

### **Packaging Information & Mounting Pad Layout**









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